



100V N-Channel MOSFET

Voltage

100 V

Current

10 A

Features

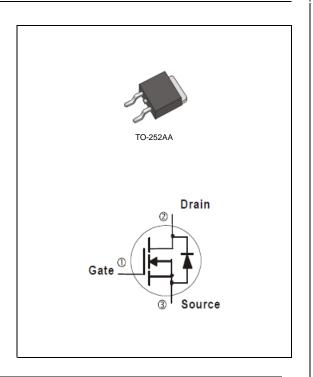
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@5A < 130m\Omega$
- $R_{DS(ON)}$, $V_{GS}@6V$, $I_{D}@2A$ <135m Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	ΓER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V_{GS}	<u>+</u> 25	V
Continuous Drain Current	T _C =25°C	I _D	10	
	T _C =100°C		6.5	А
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	40	
Power Dissipation	T _C =25°C	Po	34.7	107
	T _C =100°C		14	W
Continuous Drain Current	T _A =25°C	I _D	2.6	А
	T _A =70°C		2.1	А
Power Dissipation	T _A =25°C	-	2.0	107
Power Dissipation	T _A =70°C	Po	1.3	W
Single Pulse Avalanche Energy (Note 6)		E _{AS}	6	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	3.6	0000
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250uA	2.0	2.76	3.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS}=10V,I_{D}=5A$	-	110	130	mΩ	
Dialii-Source Oii-State Resistance		$V_{GS}=6V,I_{D}=2A$	-	120	135		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	0.01	1.0	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 20	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V_{DS} =37.5V, I_{D} =5A, V_{GS} =10V (Note 2,3)	-	12	-	nC	
Gate-Source Charge	Q_gs		-	3.1	-		
Gate-Drain Charge	Q_{gd}		-	2.2	-		
Input Capacitance	Ciss	V _{DS} =30V, V _{GS} =0V, f=1.0MHZ	-	707	-	pF	
Output Capacitance	Coss		-	40	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	16	-		
Turn-On Delay Time	td _(on)	V_{DS} =37.5V,RL=7.5 Ω ,	-	6	-		
Turn-On Rise Time	t _r	V_{GS} =10V, R_{G} =3 Ω	-	27	-	ns	
Turn-Off Delay Time	td _(off)		-	15	-		
Turn-Off Fall Time	t _f		-	7	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı				10	Α	
Diode Forward Current	I _S		-	-	10	^	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.76	1.0	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ=25°C.
- 4. The maximum current rating is package limited
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =11A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

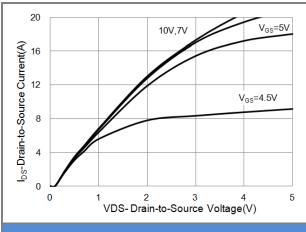


Fig.1 On-Region Characteristics

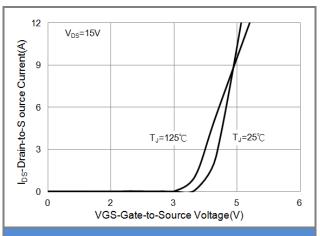


Fig.2 Transfer Characteristics

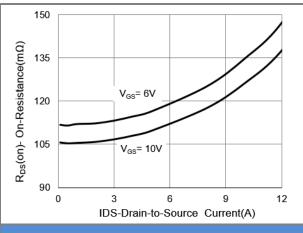


Fig.3 On-Resistance vs. Drain Current

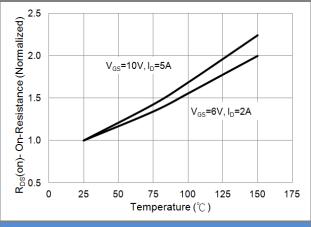


Fig.4 On-Resistance vs. Junction temperature

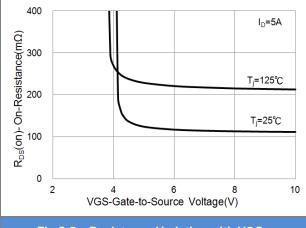


Fig.5 On-Resistance Variation with VGS.

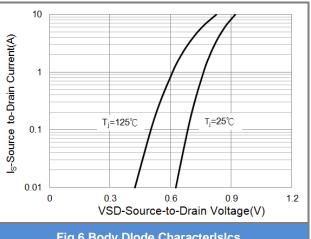


Fig.6 Body Dlode CharacterIslcs





TYPICAL CHARACTERISTIC CURVES

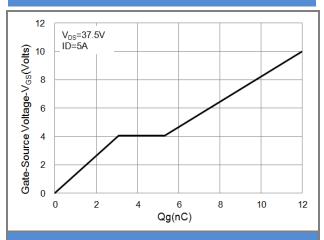


Fig.7 Gate-Charge Characteristics

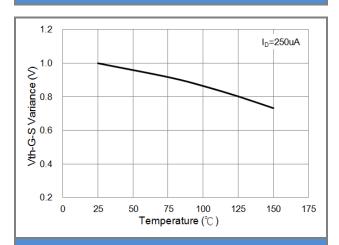
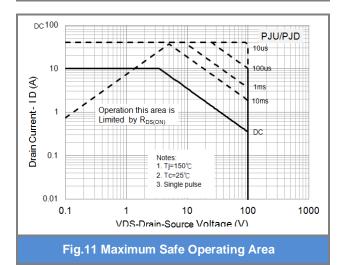


Fig.9 Threshold Voltage Variation with Temperature



1.2 I_D=250uA I_D=25

Fig.8 Breakdown Voltage Variation vs. Temperature

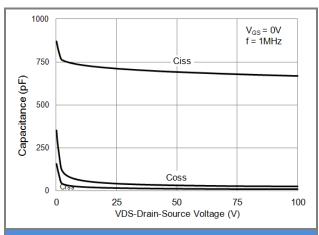


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

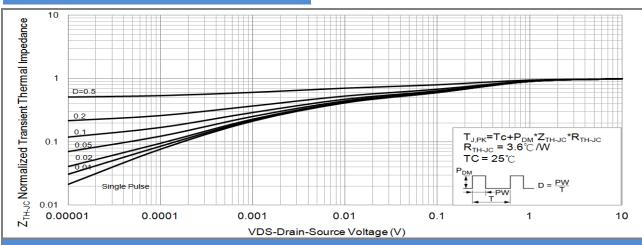
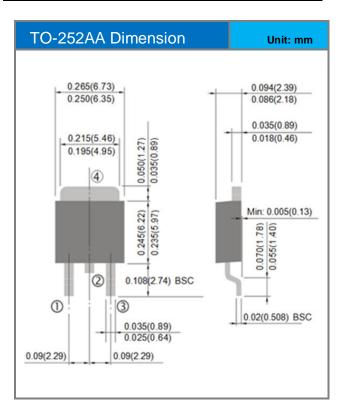


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



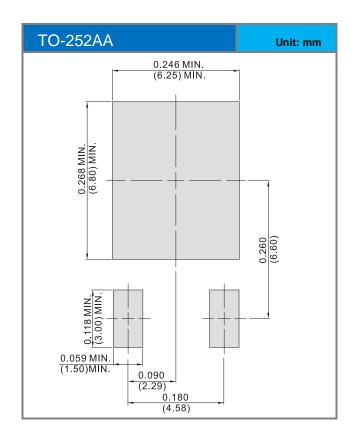




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD10N10_L2_00001	TO-252AA	3,000pcs / 13" reel	D10N10	Halogen free	

MOUNTING PAD LAYOUT







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